Peak gate current (t_p=20 s , T_j=150)	I_{GM}	5	A
Average gate power dissipation (T_j=150)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	20	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	0.5	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	V_D				

ORDERING INFORMATION

TYN 12 H -800 C

- TYN: SCRs
- 12: $I_{T(AV)}$:12A
- H: High junction temperature
- -800: V_{DRM} /V_{RRM} •800V
- C: C:TO-220C

MARKING

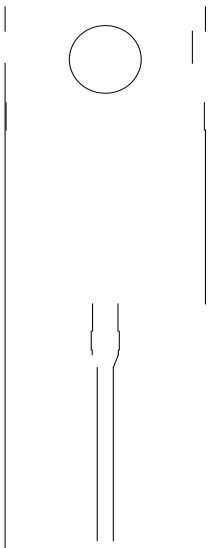

FIG.1: Maximum power dissipation versus RMS on-state current

FIG.2: RMS on-state current versus case temperature

FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards.

TYN12H-800C

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